

Vishay Siliconix

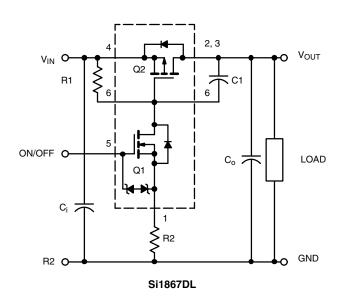
Load Switch with Level-Shift

PRODUCT SUMMARY			
V _{DS2} (V)	R_{DS(on)} (Ω)	I _D (A)	
1.8 to 8	0.600 at V _{IN} = 4.5 V	± 0.6	
	0.850 at V _{IN} = 2.5 V	± 0.5	
	1.200 at V _{IN} = 1.8 V	± 0.2	

DESCRIPTION

The Si1867DL includes a p- and n-channel MOSFET in a single SC70-6 package. The low on-resistance p-channel TrenchFET is tailored for use as a load switch. The n-Channel, with an external resistor, can be used as a level-shift to drive the P-Channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1867DL operates on supply lines from 1.8 V to 8 V, and can drive loads up to 0.6 A.

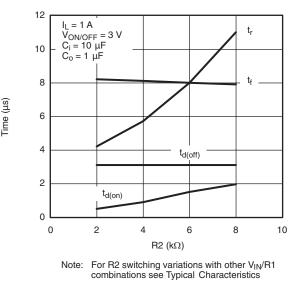
APPLICATION CIRCUITS



- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 600 mΩ Low R_{DS(on)}
- 1.8 V to 8 V Input
- 1.5 V to 8 V Logic Level Control
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

· Load Switch with Level-Shift for Portable Applications



Switching Variation R2 at V_{IN} = 2.5 V, R1 = 20 k Ω

COMPONENTS			
R1	Pull-Up Resistor	Typical 10 k Ω to 1 m Ω^{\star}	
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω^*	
C1	Optional Slew-Rate Control	Typical 1000 pF	

* Minimum R1 value should be least 10 x R2 to ensure Q1 turn-on.

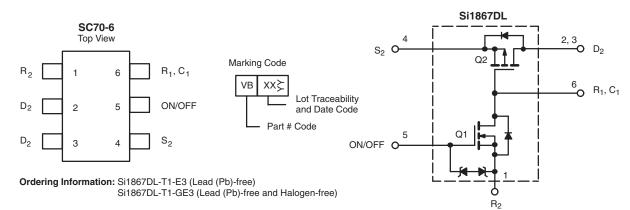
The Si1867DL is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift devices saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.



RoHS COMPLIANT HALOGEN FREE Available



FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Input Voltage		V _{IN}	8	V	
ON/OFF Voltage		V _{ON/OFF}	8		
Load Current	Continuous ^{a, b}	- I <u>L</u>	± 0.6	А	
Load Guilent	Pulsed ^{b, c}		± 3		
Continuous Intrinsic Diode Conduction ^a		۱ _S	- 0.4		
Maximum Power Dissipation ^a		PD	0.4	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
ESD Rating, MIL-STD-833D Human Body Model (100 pF, 1500 Ω)		ESD	2	kV	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient (Continuous Current) ^a	R _{thJA}	260	320	°C/W	
Maximum Junction-to-Foot (Q2)	R _{thJF}	190	230	- °C/W	

SPECIFICATIONS T _J = 25 °C unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
OFF Characteristics							
Reverse Leakage Current	I _{FL}	$V_{IN} = 8 V, V_{ON/OFF} = 0 V$			1	μA	
Diode Forward Voltage	V_{SD}	I _S = - 0.4 A		0.85	1.1	V	
ON Characteristics							
Input Voltage	V _{IN}		1.8		8	V	
On-Resistance (P-Channel) at 1 A	R _{DS(on)}	$V_{ON/OFF} = 1.5$, $V_{IN} = 4.5$ V, $I_D = 0.6$ A		0.480	0.600		
		$V_{ON/OFF} = 1.5$, $V_{IN} = 2.5$ V, $I_D = 0.5$ A		0.690	0.850	Ω	
		$V_{ON/OFF} = 1.5$, $V_{IN} = 1.8$ V, $I_D = 0.2$ A		0.950	1.200		
On-State (P-Channel) Drain-Current		$V_{\text{IN-OUT}} \leq 0.2$ V, V_{IN} = 5 V, $V_{\text{ON/OFF}}$ = 1.5 V	1			А	
	I _{D(on)}	$V_{\text{IN-OUT}} \leq 0.3$ V, V_{IN} = 3 V, $V_{\text{ON/OFF}}$ = 1.5 V	1				

Notes:

a) Surface mounted on FR4 board.

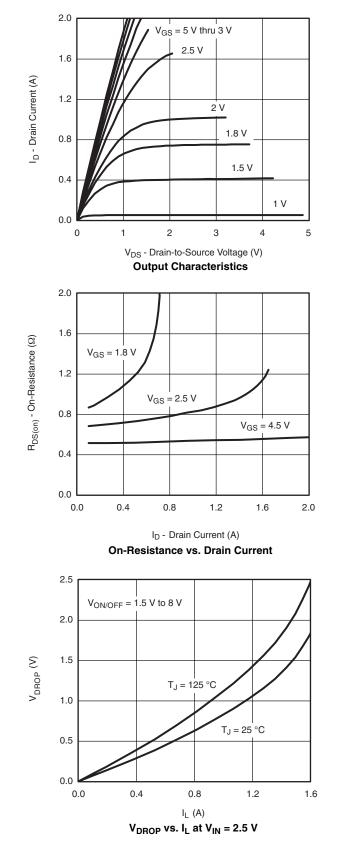
b) $V_{IN} = 8 V$, $V_{ON/OFF} = 8 V$, $T_A = 25 \text{ °C.}$ c) Pulse test; pulse width $\leq 300 \mu$ s, duty cycle $\leq 2 \%$.

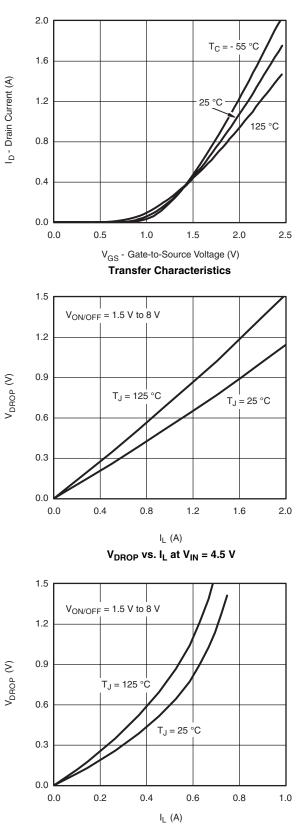
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



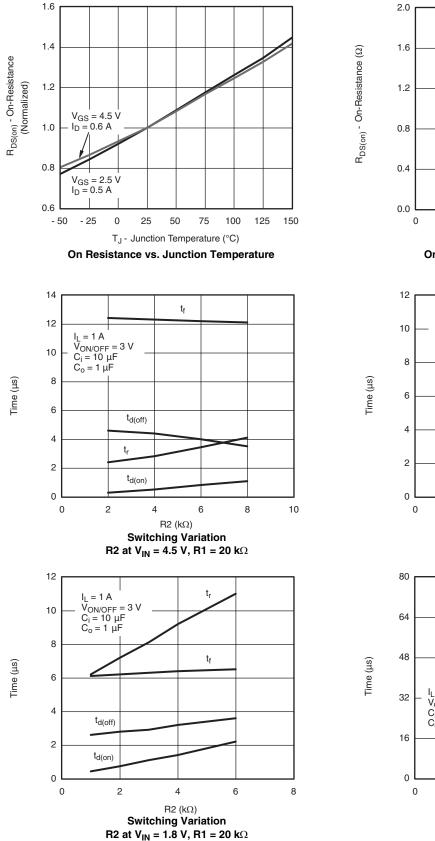


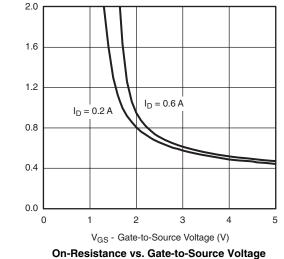
Document Number: 72534 S10-0792-Rev. D, 05-Apr-10 V_{DROP} vs. I_L at V_{IN} = 1.8 V

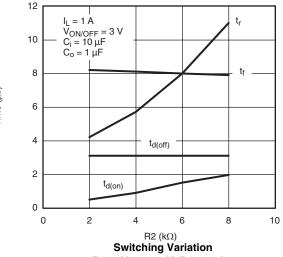
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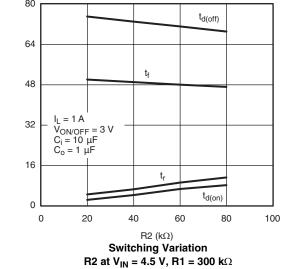
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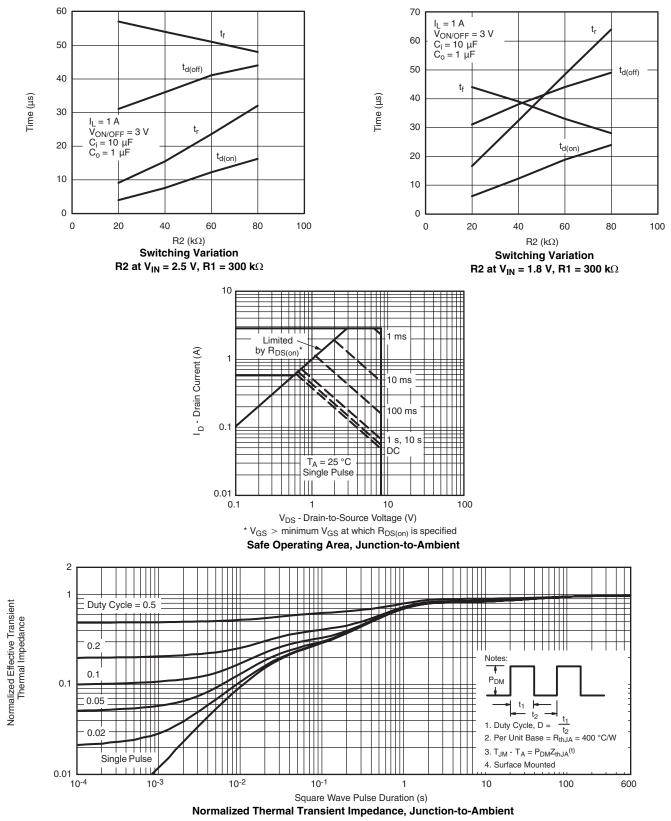
R2 at V_{IN} = 2.5 V, R1 = 20 k Ω





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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72534.



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